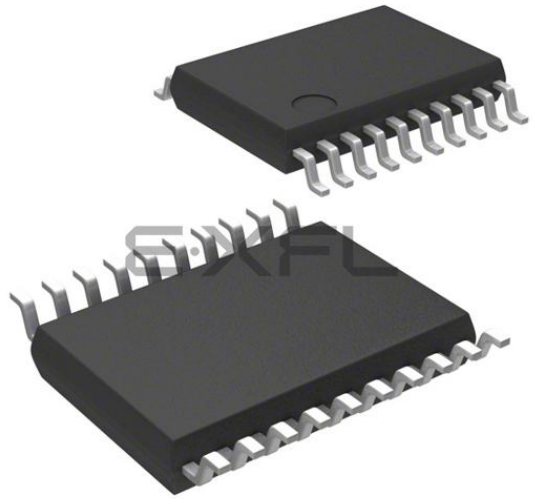

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	15
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	20-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l041f6p7

1 Introduction

The ultra-low-power STM32L041x4/6 family includes devices in 5 different package types from 20 to 48 pins. The description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L041x4/6 microcontrollers suitable for a wide range of applications:

- Gas/water meters and industrial sensors
- Healthcare and fitness equipment
- Remote control and user interface
- PC peripherals, gaming, GPS equipment
- Alarm system, wired and wireless sensors, video intercom

This STM32L041x4/6 datasheet should be read in conjunction with the STM32L0x1 reference manual (RM0377).

For information on the ARM® Cortex®-M0+ core please refer to the Cortex®-M0+ Technical Reference Manual, available from the www.arm.com website.

Figure 1 shows the general block diagram of the device family.

2 Description

The access line ultra-low-power STM32L041x4/6 family incorporates the high-performance ARM® Cortex®-M0+ 32-bit RISC core operating at a 32 MHz frequency, high-speed embedded memories (up to 32 Kbytes of Flash program memory, 1 Kbytes of data EEPROM and 8 Kbytes of RAM) plus an extensive range of enhanced I/Os and peripherals.

The STM32L041x4/6 devices provide high power efficiency for a wide range of performance. It is achieved with a large choice of internal and external clock sources, an internal voltage adaptation and several low-power modes.

The STM32L041x4/6 devices offer several analog features, one 12-bit ADC with hardware oversampling, two ultra-low-power comparators, AES, several timers, one low-power timer (LPTIM), three general-purpose 16-bit timers, one RTC and one SysTick which can be used as timebases. They also feature two watchdogs, one watchdog with independent clock and window capability and one window watchdog based on bus clock.

Moreover, the STM32L041x4/6 devices embed standard and advanced communication interfaces: one I2C, one SPI, one USART, and a low-power UART (LPUART).

The STM32L041x4/6 also include a real-time clock and a set of backup registers that remain powered in Standby mode.

The ultra-low-power STM32L041x4/6 devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +125 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.

Table 5. Functionalities depending on the working mode (from Run/active down to standby) (continued)(1)

IPs	Run/Active	Sleep	Low-power run	Low-power sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
Consumption V_{DD}=1.8 to 3.6 V (Typ)	Down to 115 µA/MHz (from Flash)	Down to 25 µA/MHz (from Flash)	Down to 6.5 µA	Down to 3.2 µA	0.35 µA (No RTC) V_{DD}=1.8 V		0.23 µA (No RTC) V_{DD}=1.8 V	
					0.6 µA (with RTC) V_{DD}=1.8 V		0.39 µA (with RTC) V_{DD}=1.8 V	
					0.38 µA (No RTC) V_{DD}=3.0 V		0.26 µA (No RTC) V_{DD}=3.0 V	
					0.8 µA (with RTC) V_{DD}=3.0 V		0.57 µA (with RTC) V_{DD}=3.0 V	

1. Legend:
   "Y" = Yes (enable).
   "O" = Optional, can be enabled/disabled by software)
   "-" = Not available
2. Some peripherals with wakeup from Stop capability can request HSI to be enabled. In this case, HSI is woken up by the peripheral, and only feeds the peripheral which requested it. HSI is automatically put off when the peripheral does not need it anymore.
3. UART and LPUART reception is functional in Stop mode. It generates a wakeup interrupt on Start.To generate a wakeup on address match or received frame event, the LPUART can run on LSE clock while the UART has to wake up or keep running the HSI clock.
4. I2C address detection is functional in Stop mode. It generates a wakeup interrupt in case of address match. It will wake up the HSI during reception.

3.2 Interconnect matrix

Several peripherals are directly interconnected. This allows autonomous communication between peripherals, thus saving CPU resources and power consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, Low-power run, Low-power sleep and Stop modes.

Table 6. STM32L0xx peripherals interconnect matrix

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop
COMPx	TIM2,TIM21, TIM22	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	-
	LPTIM	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	Y
TIMx	TIMx	Timer triggered by other timer	Y	Y	Y	Y	-

3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wakeup from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 26 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 38 GPIOs can be connected to the 16 configurable interrupt/event lines. The 10 other lines are connected to PVD, RTC, USART, I2C, LPUART, LPTIMER or comparator events.

3.15.2 Low-power Timer (LPTIM)

The low-power timer has an independent clock and is running also in Stop mode if it is clocked by LSE, LSI or an external clock. It is able to wakeup the devices from Stop mode.

This low-power timer supports the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- Continuous / one shot mode
- Selectable software / hardware input trigger
- Selectable clock source
  - Internal clock source: LSE, LSI, HSI or APB clock
  - External clock source over LPTIM input (working even with no internal clock source running, used by the Pulse Counter Application)
- Programmable digital glitch filter
- Encoder mode

3.15.3 SysTick timer

This timer is dedicated to the OS, but could also be used as a standard downcounter. It is based on a 24-bit downcounter with autoreload capability and a programmable clock source. It features a maskable system interrupt generation when the counter reaches ‘0’.

3.15.4 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 37 kHz internal RC and, as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

3.15.5 Window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

having an extremely low energy consumption. Higher speed clock can be used to reach higher baudrates.

LPUART interface can be served by the DMA controller.

3.16.4 Serial peripheral interface (SPI)

The SPI is able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

The USARTs with synchronous capability can also be used as SPI master.

The SPI can be served by the DMA controller.

Refer to *Table 13* for the supported modes and features of SPI interface.

Table 13. SPI implementation

SPI features(1)	SPI1
Hardware CRC calculation	X
I2S mode	-
TI mode	X

1. X = supported.

3.17 Cyclic redundancy check (CRC) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at linktime and stored at a given memory location.

3.18 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

6.3 Operating conditions

6.3.1 General operating conditions

Table 20. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	32	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	32	
f_{PCLK2}	Internal APB2 clock frequency	-	0	32	
V_{DD}	Standard operating voltage	BOR detector disabled	1.65	3.6	V
		BOR detector enabled, at power on	1.8	3.6	
		BOR detector disabled, after power on	1.65	3.6	
V_{DDA}	Analog operating voltage (all features)	Must be the same voltage as V_{DD}(1)	1.65	3.6	V
V_{IN}	Input voltage on FT, FTf and RST pins(2)	2.0 V ≤V_{DD} ≤3.6 V	-0.3	5.5	V
		1.65 V ≤V_{DD} ≤2.0 V	-0.3	5.2	
	Input voltage on BOOT0 pin	-	0	5.5	
	Input voltage on TC pin	-	-0.3	V_{DD}+0.3	
P_D	Power dissipation at T_A = 85 °C (range 6) or T_A =105 °C (rage 7) (3)	LQFP48 package	-	351	mW
		LQFP32 package	-	333	
		UFQFPN32 package	-	513	
		UFQFPN28 package	-	167	
		WLCSP25 package	-	286	
		TSSOP20 package	-	333	
	Power dissipation at T_A = 125 °C (range 3) (3)	LQFP48 package	-	88	
		LQFP32 package	-	83	
		UFQFPN32 package	-	128	
		UFQFPN28 package	-	42	
		WLCSP25 package	-	71	
		TSSOP20 package	-	83	

6.3.3 Embedded internal reference voltage

The parameters given in *Table 23* are based on characterization results, unless otherwise specified.

Table 22. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C, V_{DDA}= 3 V	0x1FF8 0078 - 0x1FF8 0079

Table 23. Embedded internal reference voltage(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{REFINT\ out}$(2)	Internal reference voltage	– 40 °C < T_J < +125 °C	1.202	1.224	1.242	V
$T_{VREFINT}$	Internal reference startup time	-	-	2	3	ms
V_{VREF_MEAS}	V_{DDA} voltage during V_{REFINT} factory measure	-	2.99	3	3.01	V
A_{VREF_MEAS}	Accuracy of factory-measured V_{REFINT} value(3)	Including uncertainties due to ADC and V_{DDA} values	-	-	±5	mV
T_{Coeff}(4)	Temperature coefficient	–40 °C < T_J < +125 °C	-	25	100	ppm/°C
A_{Coeff}(4)	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
$V_{DDCoeff}$(4)	Voltage coefficient	3.0 V < V_{DDA} < 3.6 V	-	-	2000	ppm/V
$T_{S\_vrefint}$(4)(5)	ADC sampling time when reading the internal reference voltage	-	5	10	-	µs
T_{ADC_BUF}(4)	Startup time of reference voltage buffer for ADC	-	-	-	10	µs
I_{BUF_ADC}(4)	Consumption of reference voltage buffer for ADC	-	-	13.5	25	µA
I_{VREF_OUT}(4)	VREF_OUT output current(6)	-	-	-	1	µA
C_{VREF_OUT}(4)	VREF_OUT output load	-	-	-	50	pF
I_{LPBUF}(4)	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V_{REFINT_DIV1}(4)	1/4 reference voltage	-	24	25	26	% V_{REFINT}
V_{REFINT_DIV2}(4)	1/2 reference voltage	-	49	50	51	
V_{REFINT_DIV3}(4)	3/4 reference voltage	-	74	75	76	

1. Refer to *Table 35: Peripheral current consumption in Stop and Standby mode* for the value of the internal reference current consumption (I_{REFINT}).
2. Guaranteed by test in production.
3. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.
4. Guaranteed by design.
5. Shortest sampling time can be determined in the application by multiple iterations.
6. To guarantee less than 1% VREF_OUT deviation.

Table 32. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
I_{DD} (Standby)	Supply current in Standby mode	Independent watchdog and LSI enabled	T_A = -40 °C to 25 °C	0.8	1.6	µA
			T_A = 55 °C	0.9	1.8	
			T_A= 85 °C	1	2	
			T_A = 105 °C	1.3	3	
			T_A = 125 °C	2.15	7	
		Independent watchdog and LSI off	T_A = -40 °C to 25 °C	0.255	0.6	
			T_A = 55 °C	0.28	0.7	
			T_A = 85 °C	0.405	1	
			T_A = 105 °C	0.7	1.7	
			T_A = 125 °C	1.55	5	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified

Table 33. Average current consumption during wakeup

Symbol	parameter	System frequency	Current consumption during wakeup	Unit
I_{DD} (WU from Stop)	Supply current during wakeup from Stop mode	HSI	1	mA
		HSI/4	0.7	
		MSI 4,2 MHz	0.7	
		MSI 1,05 MHz	0.4	
		MSI 65 KHz	0.1	
I_{DD} (Reset)	Reset pin pulled down	-	0.21	
I_{DD} (Power Up)	BOR on	-	0.23	
I_{DD} (WU from StandBy)	With Fast wakeup set	MSI 2,1 MHz	0.5	
	With Fast wakeup disabled	MSI 2,1 MHz	0.12	

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 25 MHz crystal/ceramic resonator oscillator (LQFP48 package only). All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 39*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 39. HSE oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	1		25	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
G_m	Maximum critical crystal transconductance	Startup	-	-	700	µA /V
$t_{SU(HSE)}$ (2)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design.
2. Guaranteed by characterization results. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 22*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}. Refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Figure 22. HSE oscillator circuit diagram

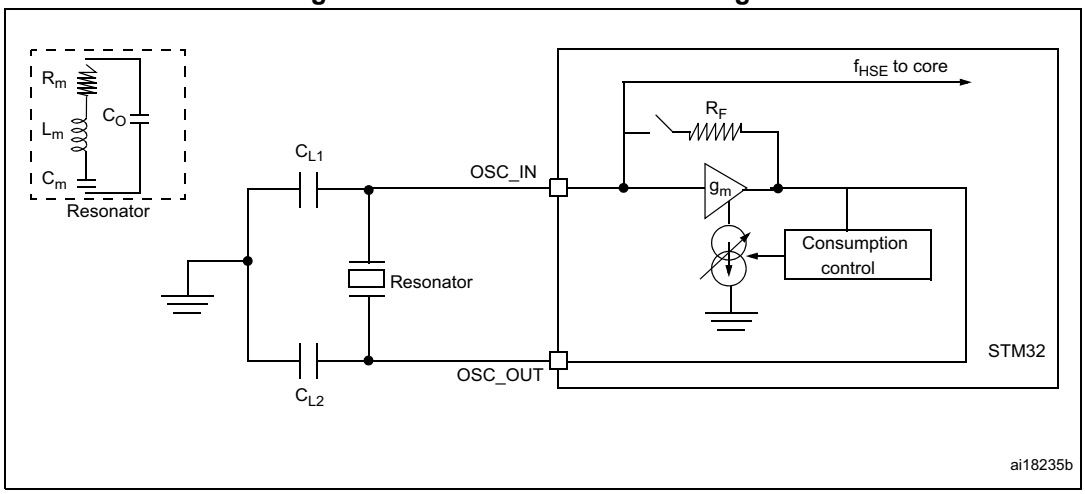


Table 44. PLL characteristics (continued)

Symbol	Parameter	Value			Unit
		Min	Typ	Max(1)	
f_{PLL_OUT}	PLL output clock	2	-	32	MHz
t_{LOCK}	PLL input = 16 MHz PLL VCO = 96 MHz	-	115	160	µs
Jitter	Cycle-to-cycle jitter	-		±600	ps
I_{DDA}(PLL)	Current consumption on V_{DDA}	-	220	450	µA
I_{DD}(PLL)	Current consumption on V_{DD}	-	120	150	

1. Guaranteed by characterization results.
2. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT}.

6.3.9 Memory characteristics

RAM memory

Table 45. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRM	Data retention mode(1)	STOP mode (or RESET)	1.65	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Flash memory and data EEPROM

Table 46. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
V_{DD}	Operating voltage Read / Write / Erase	-	1.65	-	3.6	V
t_{prog}	Programming time for word or half-page	Erasing	-	3.28	3.94	ms
		Programming	-	3.28	3.94	
I_{DD}	Average current during the whole programming / erase operation	T_A = 25 °C, V_{DD} = 3.6 V	-	500	700	µA
	Maximum current (peak) during the whole programming / erase operation		-	1.5	2.5	mA

1. Guaranteed by design.

Table 47. Flash memory and data EEPROM endurance and retention

Symbol	Parameter	Conditions	Value	Unit
			Min(1)	
N_{CYC}(2)	Cycling (erase / write) Program memory	T_A = -40°C to 105 °C	10	kcycles
	Cycling (erase / write) EEPROM data memory		100	
	Cycling (erase / write) Program memory	T_A = -40°C to 125 °C	0.2	
	Cycling (erase / write) EEPROM data memory		2	
t_{RET}(2)	Data retention (program memory) after 10 kcycles at T_A = 85 °C	T_{RET} = +85 °C	30	years
	Data retention (EEPROM data memory) after 100 kcycles at T_A = 85 °C		30	
	Data retention (program memory) after 10 kcycles at T_A = 105 °C	T_{RET} = +105 °C	10	
	Data retention (EEPROM data memory) after 100 kcycles at T_A = 105 °C			
	Data retention (program memory) after 200 cycles at T_A = 125 °C	T_{RET} = +125 °C		
	Data retention (EEPROM data memory) after 2 kcycles at T_A = 125 °C			

1. Guaranteed by characterization results.
2. Characterization is done according to JEDEC JESD22-A117.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 49. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. f_{OSC}/f_{CPU}	Unit
				8 MHz/32 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP48 package conforming to IEC61967-2	0.1 to 30 MHz	-10	dBµV
			30 to 130 MHz	5	
			130 MHz to 1GHz	-5	
			EMI Level	1.5	-

6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 50. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to ANSI/JEDEC JS-001	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1.	C4	500	

1. Guaranteed by characterization results.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 27* and *Table 55*, respectively.

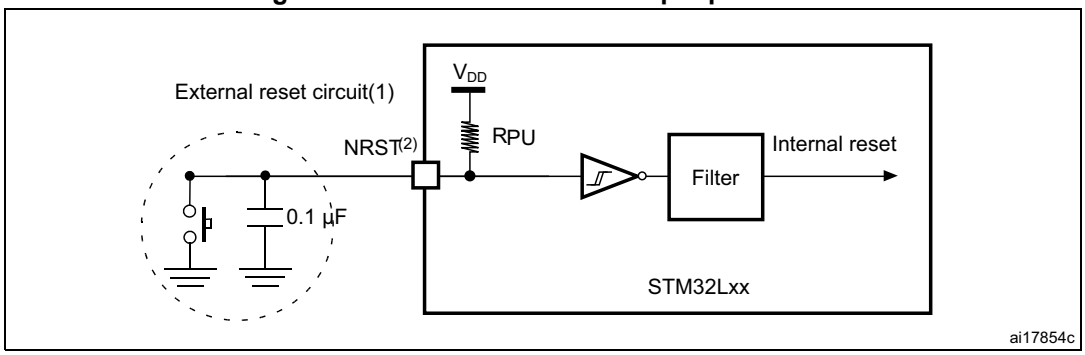
Unless otherwise specified, the parameters given in *Table 55* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

Table 55. I/O AC characteristics(1)

OSPEEDRx [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Max(2)	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	100	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	320	
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	0.6	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	30	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	65	
10	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	13	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	28	
11	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	35	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	10	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	6	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	17	
Fm+ configuration(4)	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.5 V to 3.6 V	-	1	MHz
	$t_{f(IO)out}$	Output fall time		-	10	ns
	$t_{r(IO)out}$	Output rise time		-	30	
	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 1.65 V to 3.6 V	-	350	KHz
	$t_{f(IO)out}$	Output fall time		-	15	ns
	$t_{r(IO)out}$	Output rise time		-	60	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design.
3. The maximum frequency is defined in *Figure 27*.
4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the line reference manual for a detailed description of Fm+ I/O configuration.

Figure 28. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 56*. Otherwise the reset will not be taken into account by the device.

6.3.15 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 57* are values derived from tests performed under ambient temperature, f_{PCLK} frequency and V_{DDA} supply voltage conditions summarized in *Table 20: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

Table 57. ADC characteristics

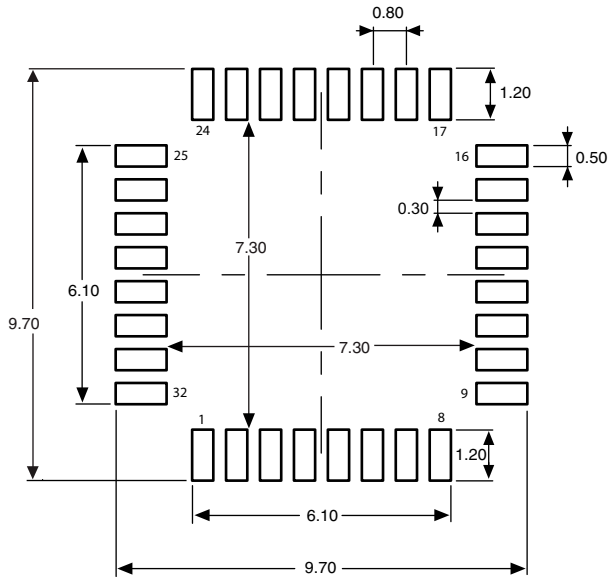
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage for ADC on	Fast channel	1.65	-	3.6	V
		Standard channel	1.75(1)	-	3.6	
$I_{DDA\ (ADC)}$	Current consumption of the ADC on V_{DDA}	1.14 Msps	-	200	-	µA
		10 ksps	-	40	-	
	Current consumption of the ADC on V_{DD}(2)	1.14 Msps	-	70	-	
		10 ksps	-	1	-	
f_{ADC}	ADC clock frequency	Voltage scaling Range 1	0.14	-	16	MHz
		Voltage scaling Range 2	0.14	-	8	
		Voltage scaling Range 3	0.14	-	4	
f_S(3)	Sampling rate		0.05	-	1.14	MHz
f_{TRIG}(3)	External trigger frequency	f_{ADC} = 16 MHz	-	-	941	kHz
			-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range		0	-	V_{DDA}	V
R_{AIN}(3)	External input impedance	See *Equation 1* and *Table 58* for details	-	-	50	kΩ
R_{ADC}(3)(4)	Sampling switch resistance		-	-	1	kΩ
C_{ADC}(3)	Internal sample and hold capacitor		-	-	8	pF

Table 71. LQFP32, 7 x 7 mm, 32-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.300	0.370	0.450	0.0118	0.0146	0.0177
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.600	-	-	0.2205	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.600	-	-	0.2205	-
e	-	0.800	-	-	0.0315	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.100	-	-	0.0039
A	-	-	1.600	-	-	0.0630

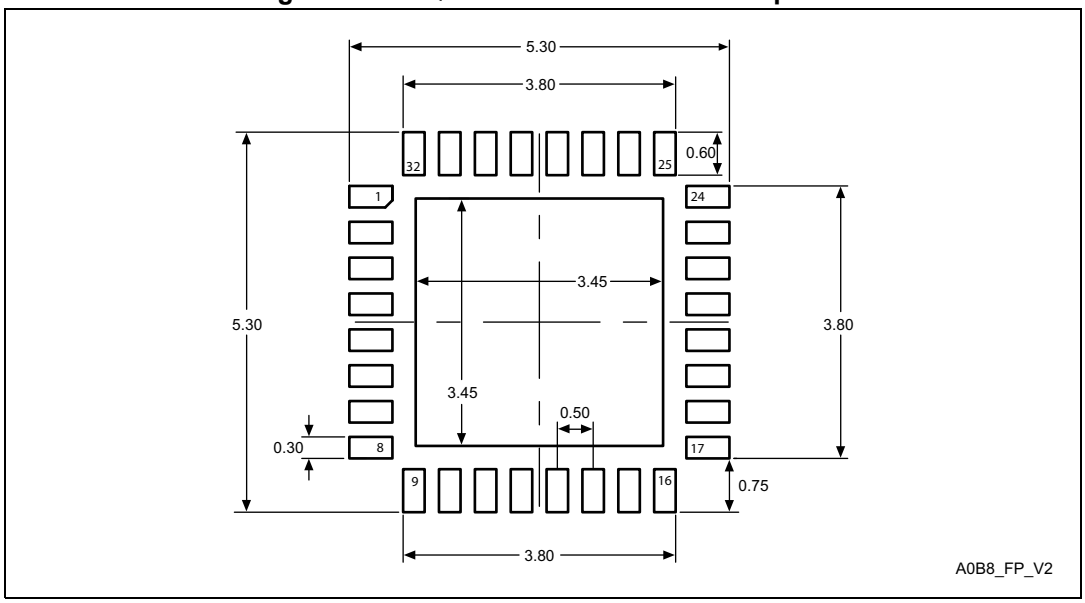
1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 38. LQFP32 recommended footprint



1. Dimensions are expressed in millimeters.

Figure 41. UFQFPN32 recommended footprint



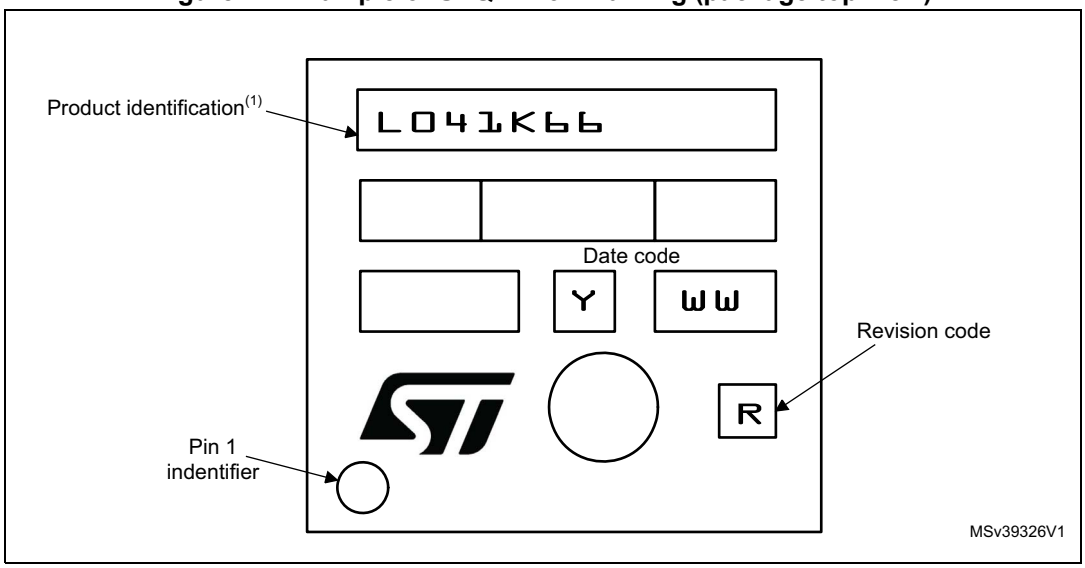
1. Dimensions are expressed in millimeters.

UFQFPN32 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depends assembly location, are not indicated below.

Figure 42. Example of UFQFPN32 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

8 Part numbering

Table 78. STM32L041x4/6 ordering information scheme

Example: STM32 L 041 K 6 T 6 D TR

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

L = Low power

Device subfamily

041 = Access line with AES

Pin count

C = 48 pins
K = 32 pins
G = 28 pins
E = 25 pins
F = 20 pins

Flash memory size

4 = 16 Kbytes
6 = 32 Kbytes

Package

T = LQFP
U = UFQFPN
Y = WLCSP
P = TSSOP

Temperature range

6 = Industrial temperature range, –40 to 85 °C
7 = Industrial temperature range, –40 to 105 °C
3 = Industrial temperature range, –40 to 125 °C

Number of UFQFPN28 power pairs

S = one power pair(1)
No character = Two power pairs

Options

No character = V_{DD} range: 1.8 to 3.6 V and BOR enabled
D = V_{DD} range: 1.65 to 3.6 V and BOR disabled

Packing

TR = tape and reel
No character = tray or tube

1. This option is available only on STM32L041GxUxS part number. Contact your nearest ST sales office for availability.

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.